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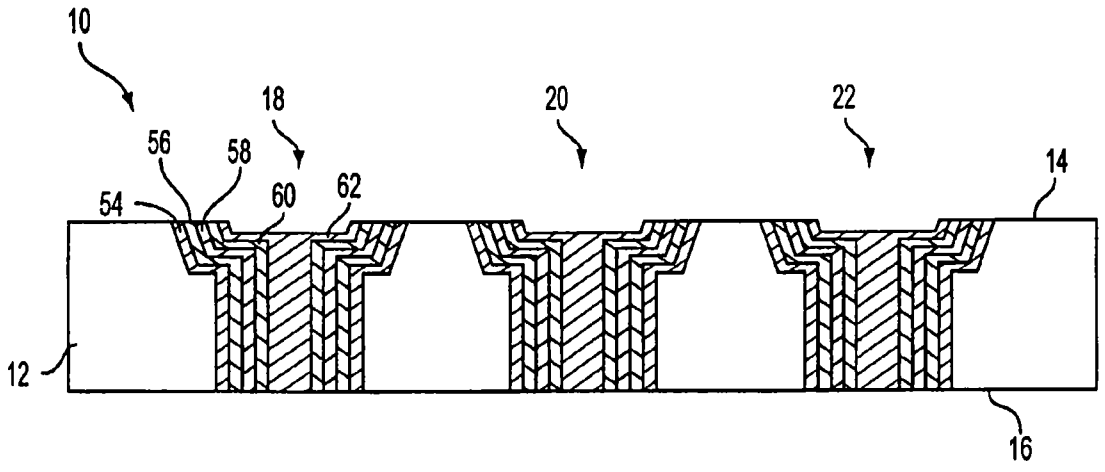
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(54) Title: HIGH PERFORMANCE SILICON CONTACT FOR FLIP CHIP



(57) Abstract: The present invention provides a semiconductive substrate (12) which includes front (14) and back surfaces (16) and a hole (18, 20, 22) which extends through the substrate and between the front (14) and back surfaces (16). The hole (18, 20, 22) is defined in part by an interior wall portion and forms an outer conductive sheath. Conductive material (54) is formed proximate at least some of the interior wall portion. Subsequently, a layer of dielectric material (56) is formed within the hole, over and radially inwardly of the conductive material. A second conductive material (60) is then formed within the hole over and radially inwardly of the dielectric material layer (56). The latter conductive material constitutes an inner conductive coaxial line component.

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